

L Number	Hits	Search Text	DB	Time stamp
1	7275	((438/197) or (438/217) or (438/266) or (438/267) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/311) or (438/359) or (438/369) or (438/371) or (438/491) or (438/532) or (438/564)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 17:18
2	5023	double near2 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 17:19
3	32224	soi or (silicon near2 insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 17:19
4	148	finfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 17:20
5	751	(double near2 gate) and (soi or (silicon near2 insulator))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 17:20
6	82	((double near2 gate) and (soi or (silicon near2 insulator))) and finfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 17:20
7	14	((((438/197) or (438/217) or (438/266) or (438/267) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/311) or (438/359) or (438/369) or (438/371) or (438/491) or (438/532) or (438/564)).CCLS.) and (((double near2 gate) and (soi or (silicon near2 insulator))) and finfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 17:20
-	6120	((438/197) or (438/266) or (438/267) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/311) or (438/359) or (438/369) or (438/371) or (438/491) or (438/532) or (438/564)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 17:18
-	5023	double near2 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 17:18
-	32224	soi or (silicon near2 insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 17:19
-	38	finfet near2 transistor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 17:19
-	751	(double near2 gate) and (soi or (silicon near2 insulator))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 13:09

	0	((double near2 gate) and (soi or (silicon near2 insulator))) and (finfet near2 transistor\$1)) and (((438/197) or (438/266) or (438/267) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/311) or (438/359) or (438/369) or (438/371) or (438/491) or (438/532) or (438/564)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 13:09
	23	((double near2 gate) and (soi or (silicon near2 insulator))) and (finfet near2 transistor\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 13:11
	16	((double near2 gate) and (soi or (silicon near2 insulator))) and (finfet near2 transistor\$1)) and (ion near2 implant\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 13:15
	425	((double near2 gate) and (soi or (silicon near2 insulator))) and (ion near2 implant\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 15:59
	24	((double near2 gate) and (soi or (silicon near2 insulator))) and (ion near2 implant\$5)) and (((438/197) or (438/266) or (438/267) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/311) or (438/359) or (438/369) or (438/371) or (438/491) or (438/532) or (438/564)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 13:29
	11	("5500379" "5516711" "5750435" "5793090" "5891774" "6083795" "6297098" "6300182" "6413802" "6509264" "6521502" "2002/0195626").PN.	USPAT	2004/09/29 13:18
	16	(finfet near2 transistor\$1) and (ion near2 implant\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 13:20
	80	((double near2 gate) and (soi or (silicon near2 insulator))) and (ion near2 implant\$5)) and recess\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 13:29
	148	finfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 14:00
	5	finfet and ((recess\$2 or undercut\$4) near2 ((buried near2 oxide) or insulat\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 14:00
	9	finfet and ((recess\$2 or undercut\$4) near5 ((box or (buried near2 oxide)) or insulat\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 13:57
	139	finfet not (finfet and ((recess\$2 or undercut\$4) near5 ((box or (buried near2 oxide)) or insulat\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 13:57
	115	finfet and (soi or (silicon near2 insulator))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 14:00

-	4	("6010934" "6117711" "6252284" "6657259" "2002/0197781").PN.	USPAT	2004/09/29 14:21
-	0	6770516.URPN.	USPAT	2004/09/29 14:22
-	3	("6010934") or ("6117711") or ("6252284").PN.	USPAT	2004/09/29 15:21
-	425	((double near2 gate) and (soi or (silicon near2 insulator))) and (ion near2 implant\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/29 15:59
-	137	((double near2 gate) and (soi or (silicon near2 insulator))) and (ion near2 implant\$5)) and (poly\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/29 16:00